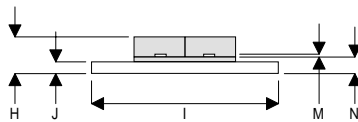
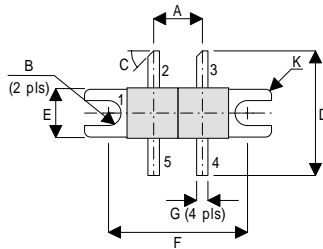


MECHANICAL DATA

**GOLD METALLISED
MULTI-PURPOSE SILICON
DMOS RF FET
80W – 28V – 500MHz
PUSH-PULL**



DK

PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1
 PIN 3 DRAIN 2 PIN 4 GATE 2
 PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
A	6.45	0.13	0.254	0.005
B	1.65R	0.13	0.065R	0.005
C	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
E	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
H	4.82	0.25	0.190	0.010
I	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
M	0.13	0.02	0.005	0.001
N	2.16	0.13	0.085	0.005

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 13 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from 1 MHz to 500 MHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	175W
BV_{DSS}	Drain – Source Breakdown Voltage *	70V
BV_{GSS}	Gate – Source Breakdown Voltage *	±20V
$I_{D(sat)}$	Drain Current *	10A
T_{stg}	Storage Temperature	-65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

* Per Side

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
PER SIDE						
B _V DSS	Drain–Source Breakdown Voltage	V _{GS} = 0	I _D = 100mA	70	V	
I _D DSS	Zero Gate Voltage Drain Current	V _{DS} = 28V	V _{GS} = 0	2	mA	
I _G DSS	Gate Leakage Current	V _{GS} = 20V	V _{DS} = 0	1	μA	
V _{GS(th)}	Gate Threshold Voltage *	I _D = 10mA	V _{DS} = V _{GS}	1	7	V
g _{fs}	Forward Transconductance *	V _{DS} = 10V	I _D = 2A	1.6	S	
TOTAL DEVICE						
G _{PS}	Common Source Power Gain	P _O = 80W		13	dB	
η	Drain Efficiency	V _{DS} = 28V	I _{DQ} = 0.4A	50	%	
VSWR	Load Mismatch Tolerance	f = 400MHz		20:1	—	
PER SIDE						
C _i SS	Input Capacitance	V _{DS} = 28V	V _{GS} = -5V f = 1MHz		120	pF
C _o SS	Output Capacitance	V _{DS} = 28V	V _{GS} = 0 f = 1MHz		60	pF
C _r SS	Reverse Transfer Capacitance	V _{DS} = 28V	V _{GS} = 0 f = 1MHz		5	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 1.0°C / W
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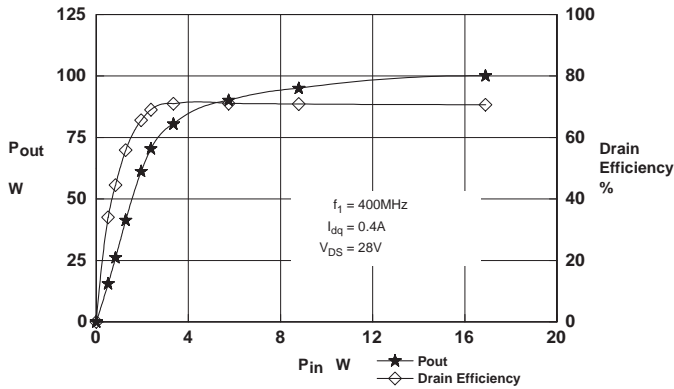


Figure 1 – Power Output and Efficiency vs. Power Input.

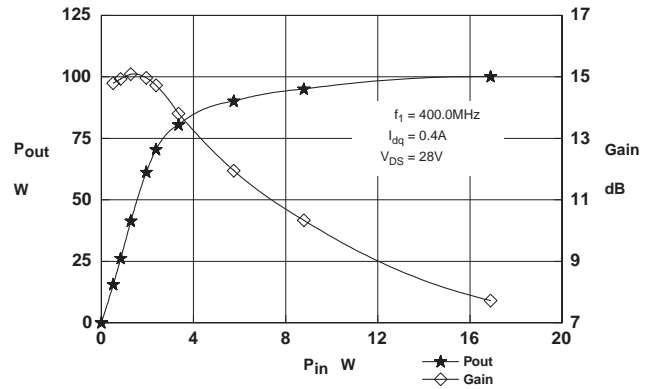


Figure 2 – Power Output & Gain vs. Power Input.

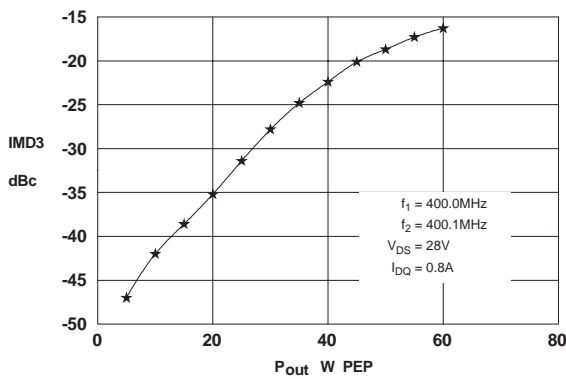


Figure 3 – IMD vs. Output Power.

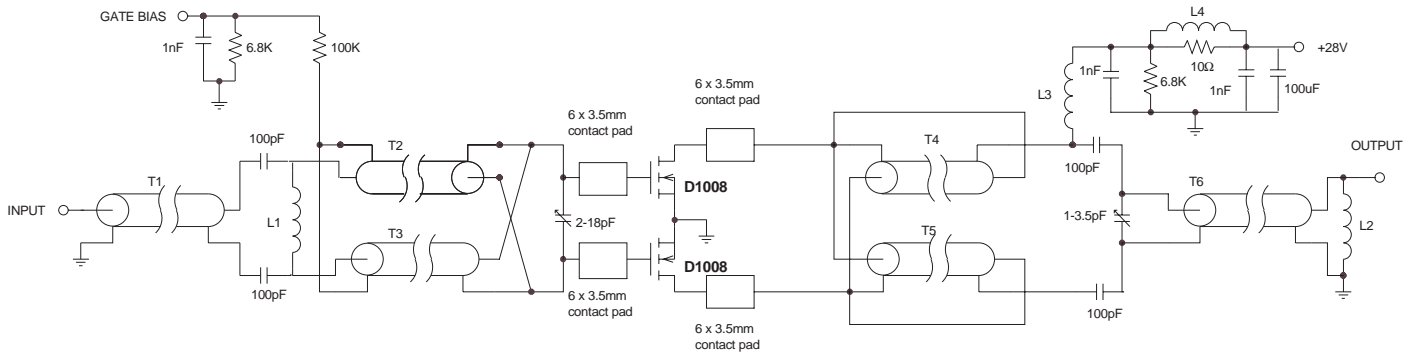
D1008UK OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z _S Ω	Z _L Ω
400	1.5 + j0.2	5.0 + j2.0

Typical S Parameters

! Vds=28V, Idq=1A
MHz S M A R 50

!Freq MHz	S11 mag ang	S21 mag ang	S12 mag ang	S22 mag ang
100	0.794 -158	14.622 69	0.0115 -7	0.61 -145
200	0.881 -167	5.821 42	0.0061 3	0.794 -156
300	0.923 -171	3.02 28	0.0068 60	0.871 -162
400	0.923 -176	1.82 18	0.117 77	0.902 -167
500	0.937 -179	1.439 15	0.0168 76	0.923 -169
600	0.952 177	1.057 13	0.0234 75	0.945 -171
700	0.966 174	0.676 10	0.0285 74	0.966 -174
800	0.966 171	0.543 5	0.0335 69	0.955 -177
900	0.977 167	0.447 1	0.0394 64	0.966 178
1000	0.966 165	0.359 1	0.0432 64	0.955 178



D1008UK TEST FIXTURE

Substrate 1.6mm PTFE/glass, Er=2.5
All microstrip lines W=4.4mm

T1	70mm	50Ω UT34 SEMI RIGID COAX	L1	3.5 turns of 24swg ECW, 3mm ID
T2,T3	85mm	25Ω UT70-25 SEMI RIGID COAX	L2	5.5 turns of 24swg ECW, 4mm ID
T4,T5	100mm	15Ω UT85-15 SEMI RIGID COAX	L3	4 turns of 21swg ECW, 7mm ID
T6	70mm	50Ω UT85 SEMI RIGID COAX	L4	3 turns of 21swg ECW on Fair-Rite FT50-75 core